

关键参数 Key Parameters

V_{CES}		1200	V
$V_{CE(sat)}$	Typ.	1.80	V
I_C	Max.	1400	A
$I_{C(RM)}$	Max.	2800	A

典型应用 Typical Applications

● 马达驱动	Motor Drives
● 大功率变流器	High Power Converters
● 风力发电	Wind Turbines
● 高可靠性逆变器	High Reliability Inverter

特点 Features

● 铜基板	Cu Baseplate
● 氧化铝衬板	Al_2O_3 Substrates
● 高热循环能力	High Thermal Cycling Capability
● 10 μ s 短路承受能力	10 μ s Short Circuit Withstand

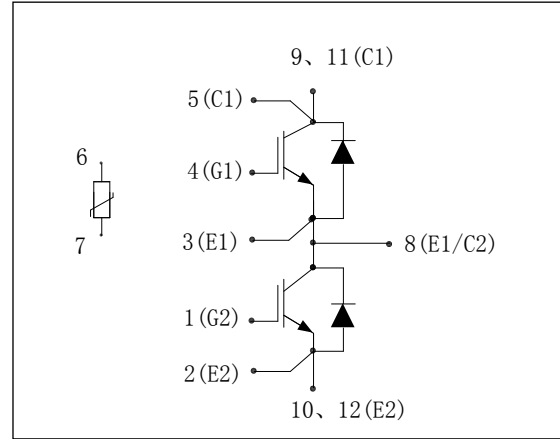
电路结构 Circuit Configuration


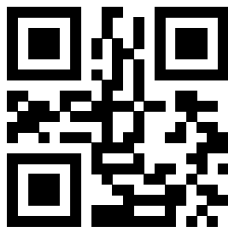
图 1. 电路结构

Fig. 1 Circuit configuration

模块外形 Module Appearance


图 2. 模块外形

Fig. 2 Module appearance

模块标签说明
Module Label Code Instruction


数据位置 Data position	数据内容 Content of data
1--4	模块生产年周 Production year and week
5--12	模块批次号 Module batch number
13--16	模块序列号 Module serial number

最大额定值
Absolute Maximum Ratings

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	数值 Value	单位 Unit
V_{CES}	集电极-发射极电压 Collector-emitter voltage	$V_{GE} = 0V, T_C = 25\text{ }^\circ\text{C}$	1200	V
V_{GES}	栅极-发射极电压 Gate-emitter voltage	$T_C = 25\text{ }^\circ\text{C}$	± 20	V
I_C	集电极电流 Collector-emitter current	$T_C = 100\text{ }^\circ\text{C}$	1400	A
$I_{C(PK)}$	集电极峰值电流 Peak collector current	$t_p = 1\text{ms}$	2800	A
P_{max}	晶体管部分最大损耗 Max. transistor power dissipation	$T_{vj} = 175\text{ }^\circ\text{C}, T_C = 25\text{ }^\circ\text{C}$	7.5	kW
ρ_t	二极管 ρ_t 值 Diode ρ_t	$V_R = 0V, t_p = 10\text{ms}, T_{vj} = 150\text{ }^\circ\text{C}$	172	kA^2s
V_{isol}	绝缘电压(模块) Isolation voltage – per module	短接所有端子, 端子与基板间施加电压 (Commoned terminals to base plate), AC RMS, 1 min, 50Hz, $T_C = 25\text{ }^\circ\text{C}$	4000	V

热和机械数据
Thermal & Mechanical Data

参数 Symbol	说明 Explanation	值 Value	单位 Unit
爬电距离 Creepage distance	端子-散热器 Terminal to heatsink	33.0	mm
	端子-端子 Terminal to terminal	33.0	mm
绝缘间隙 Clearance	端子-散热器 Terminal to heatsink	19.0	mm
	端子-端子 Terminal to terminal	19.0	mm
相对漏电起痕指数 CTI (Comparative Tracking Index)		>400	

热和机械数据 Thermal & Mechanical Data

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	最大值 Max.	单位 Unit
$R_{th(J-C)}$ IGBT	IGBT 结壳热阻 Thermal resistance – IGBT			20	K / kW
$R_{th(J-C)}$ Diode	二极管结壳热阻 Thermal resistance – Diode			35.5	K / kW
$R_{th(C-H)}$ IGBT	接触热阻(IGBT) Thermal resistance – case to heatsink (IGBT)	导热脂 1W/m·°C Mounting grease 1W/m·°C		9.5	K / kW
$R_{th(C-H)}$ Diode	接触热阻(Diode) Thermal resistance – case to heatsink (Diode)	导热脂 1W/m·°C Mounting grease 1W/m·°C		17	K / kW
$T_{vj\ op}$	工作结温 Operating junction temperature	IGBT 部分 (IGBT)	-40	150	°C
		二极管部分 (Diode)	-40	150	°C
T_{stg}	存储温度 Storage temperature range		-40	150	°C
M	安装力矩 Screw torque	安装紧固用 - M5 Mounting - M5	3	6	Nm
		电路互连用 - M8 Electrical connections - M8	8	10	Nm

热敏电阻数据
NTC-Thermistor Data

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
R_{25}	额定电阻值 Rated resistance	$T_C = 25\ ^\circ\text{C}$		5		kΩ
$\Delta R/R$	R100 偏差 Deviation of R100	$T_C = 100\ ^\circ\text{C}$, $R_{100}=493\ \Omega$	-5		5	%
P_{25}	耗散功率 Power dissipation	$T_C = 25\ ^\circ\text{C}$			20	mW
$B_{25/50}$	B-值 B-value	$R_2 = R_{25}\exp [B_{25/50}(1/T_2 - 1/(298.15\ \text{K}))]$		3375		K
$B_{25/80}$	B-值 B-value	$R_2 = R_{25}\exp [B_{25/80}(1/T_2 - 1/(298.15\ \text{K}))]$		3411		K
$B_{25/100}$	B-值 B-value	$R_2 = R_{25}\exp [B_{25/100}(1/T_2 - 1/(298.15\ \text{K}))]$		3433		K

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

注意：该器件对静电敏感，用户须采取 ESD 防护措施。

电特性值
Electrical Characteristics

 除非特别声明，否则 $T_C = 25\text{ }^\circ\text{C}$ $T_C = 25\text{ }^\circ\text{C}$ unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
I_{CES}	集电极截止电流 Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 125\text{ }^\circ\text{C}$			15	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 150\text{ }^\circ\text{C}$			30	mA
I_{GES}	栅极漏电流 Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			0.5	μA
$V_{GE(TH)}$	栅极-发射极阈值电压 Gate threshold voltage	$I_C = 60\text{mA}, V_{GE} = V_{CE}$	5.00	6.00	7.00	V
$V_{CE(sat)}^{(*1)}$	集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 1400\text{A}$		1.80	2.20	V
		$V_{GE} = 15V, I_C = 1400\text{A}, T_{vj} = 125\text{ }^\circ\text{C}$		2.15	2.55	V
		$V_{GE} = 15V, I_C = 1400\text{A}, T_{vj} = 150\text{ }^\circ\text{C}$		2.25	2.65	V
I_F	二极管正向直流电流 Diode forward current	DC		1400		A
I_{FRM}	二极管正向重复峰值电流 Diode peak forward current	$t_P = 1\text{ms}$		2800		A
$V_F^{(*1)}$	二极管正向电压 Diode forward voltage	$I_F = 1400\text{A}, V_{GE} = 0$		1.90	2.30	V
		$I_F = 1400\text{A}, V_{GE} = 0, T_{vj} = 125\text{ }^\circ\text{C}$		2.10	2.50	V
		$I_F = 1400\text{A}, V_{GE} = 0, T_{vj} = 150\text{ }^\circ\text{C}$		2.10	2.50	V
I_{SC}	短路电流 Short circuit current	$T_{vj} = 150\text{ }^\circ\text{C}, V_{CC} = 800\text{V},$ $V_{GE} \leq 15\text{V}, t_P \leq 10\mu\text{s},$ $V_{CE(max)} = V_{CES} - L^{(*2)} \times di/dt,$ IEC 6074-9		5800		A

注意: 1.(*1) 表示该参数的测试点为辅助母排端子 (*1) indicates it is measured at the auxiliary busbar terminal),
Note: 2.(*2) 表示 L 是电路杂散电感加上 L_M (*2) indicates L is the circuit stray inductance plus L_M).

电特性值
Electrical Characteristics

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符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
C_{ies}	输入电容 Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		118		nF
Q_g	栅极电荷 Gate charge	$\pm 15V$		13		μC
C_{res}	反向传输电容 Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		3.2		nF
L_M	模块电感 Module inductance			10		nH
R_{INT}	母排端子- 芯片内阻 Internal transistor resistance terminal- chip	$T_C = 25\text{ }^\circ\text{C}$		0.2		m Ω

电特性值
Electrical Characteristics

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit	
$t_{d(off)}$	关断延迟时间 Turn-off delay time	$I_C = 1400A,$ $V_{CE} = 600V,$ $V_{GE} = \pm 15V,$ $R_{G(OFF)} = 1.0\Omega,$ $L_S = 25nH,$ $dV/dt = 2100V/us$ ($T_{vj} = 150^\circ C$).	$T_{vj} = 25^\circ C$	1120		ns	
			$T_{vj} = 125^\circ C$	1160			
			$T_{vj} = 150^\circ C$	1200			
t_f	下降时间 Fall time		$T_{vj} = 25^\circ C$		230		ns
			$T_{vj} = 125^\circ C$		320		
			$T_{vj} = 150^\circ C$		340		
E_{OFF}	关断损耗 Turn-off energy loss		$T_{vj} = 25^\circ C$		245		mJ
			$T_{vj} = 125^\circ C$		276		
			$T_{vj} = 150^\circ C$		285		
$t_{d(on)}$	开通延迟时间 Turn-on delay time	$T_{vj} = 25^\circ C$		320		ns	
		$T_{vj} = 125^\circ C$		300			
		$T_{vj} = 150^\circ C$		290			
t_r	上升时间 Rise time	$T_{vj} = 25^\circ C$		165		ns	
		$T_{vj} = 125^\circ C$		180			
		$T_{vj} = 150^\circ C$		195			
E_{ON}	开通损耗 Turn-on energy loss	$T_{vj} = 25^\circ C$		160		mJ	
		$T_{vj} = 125^\circ C$		196			
		$T_{vj} = 150^\circ C$		208			
Q_{rr}	二极管反向恢复电荷 Diode reverse recovery charge	$T_{vj} = 25^\circ C$		92		μC	
		$T_{vj} = 125^\circ C$		200			
		$T_{vj} = 150^\circ C$		236			
I_{rr}	二极管反向恢复电流 Diode reverse recovery current	$T_{vj} = 25^\circ C$		580		A	
		$T_{vj} = 125^\circ C$		697			
		$T_{vj} = 150^\circ C$		765			
E_{rec}	二极管反向恢复损耗 Diode reverse recovery energy	$T_{vj} = 25^\circ C$		41		mJ	
		$T_{vj} = 125^\circ C$		90			
		$T_{vj} = 150^\circ C$		102			

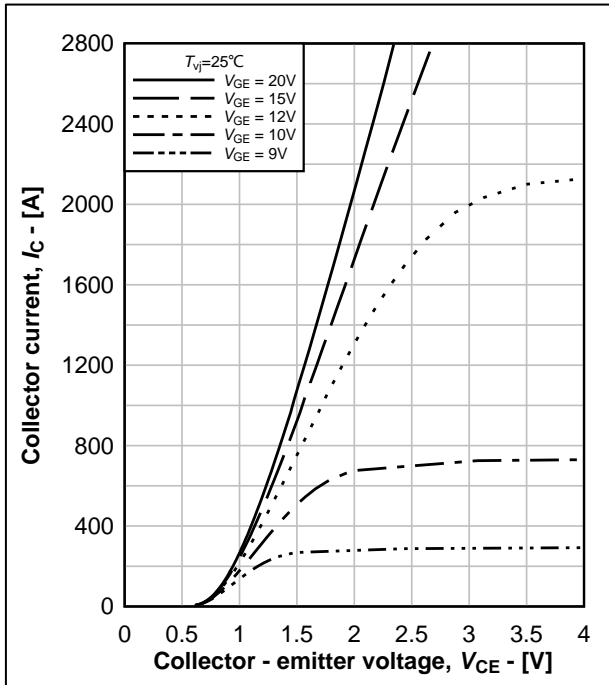

 图 3. IGBT 输出特性典型曲线, $I_c = f(V_{CE})$

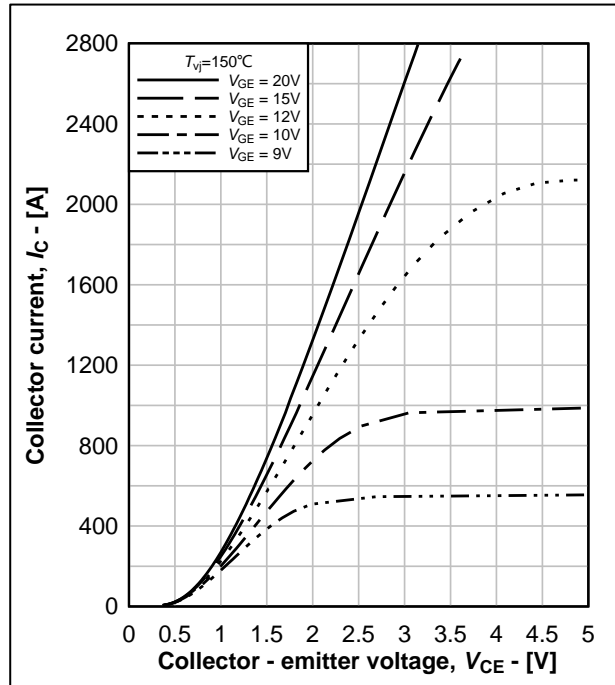
 Fig.3 Typical IGBT output characteristics, $I_c = f(V_{CE})$

 图 4. IGBT 输出特性典型曲线, $I_c = f(V_{CE})$

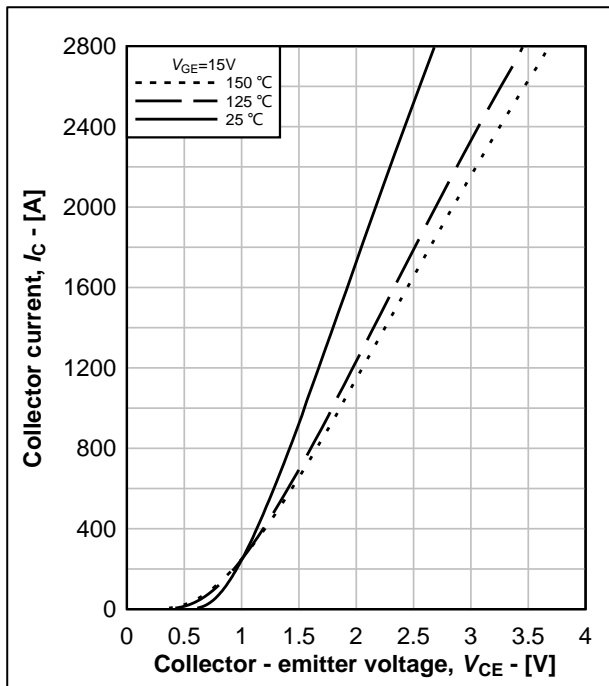
 Fig.4 Typical IGBT output characteristics, $I_c = f(V_{CE})$

 图 5. IGBT 输出特性典型曲线, $I_c = f(V_{CE})$

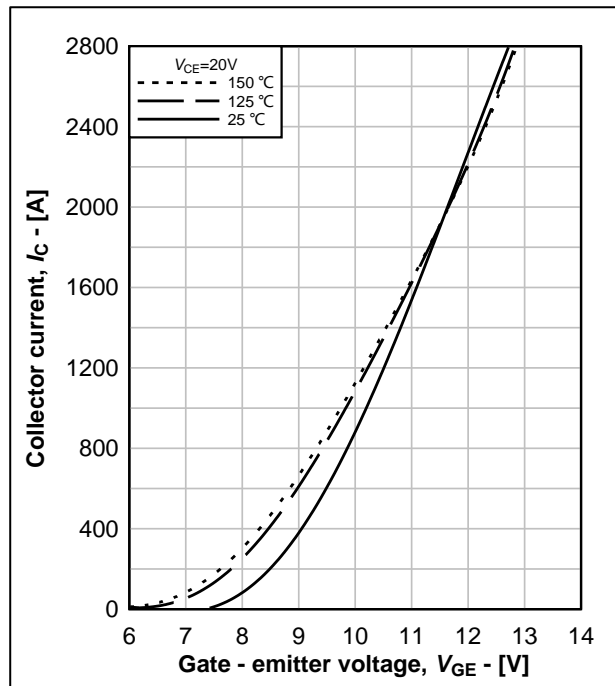
 Fig.5 Typical IGBT output characteristics, $I_c = f(V_{CE})$

 图 6. IGBT 传输特性典型曲线, $I_c = f(V_{GE})$

 Fig.6 Typical IGBT transfer characteristics, $I_c = f(V_{GE})$

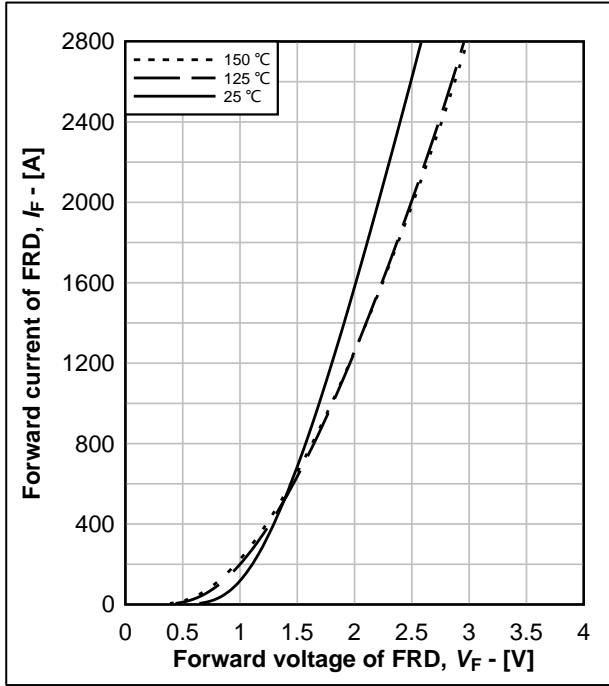


图 7. FRD 输出特性典型曲线, $I_F = f(V_F)$ Fig.7
Typical FRD output characteristics, $I_F = f(V_F)$

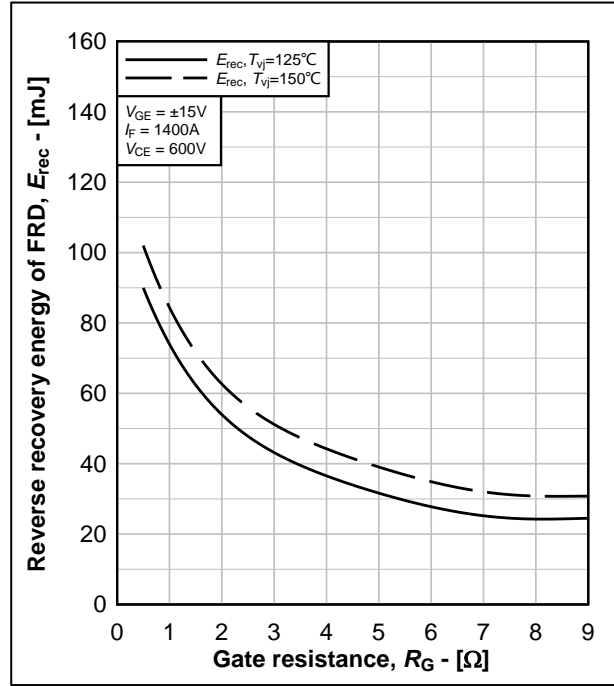


图 8. FRD 反向恢复能耗典型曲线, $E_{rec} = f(R_G)$ Fig.8
Typical FRD E_{rec} , $E_{rec} = f(R_G)$

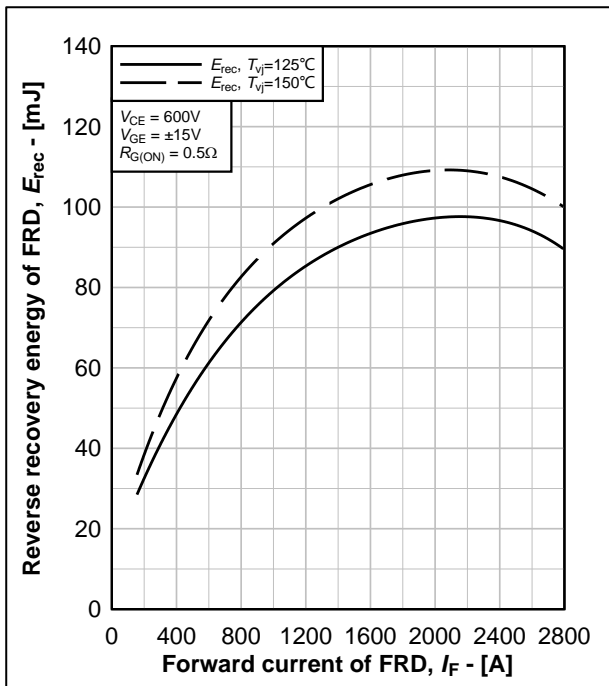


图 9. FRD 反向恢复能耗典型曲线, $E_{rec} = f(I_F)$ Fig.9
Typical FRD E_{rec} , $E_{rec} = f(I_F)$

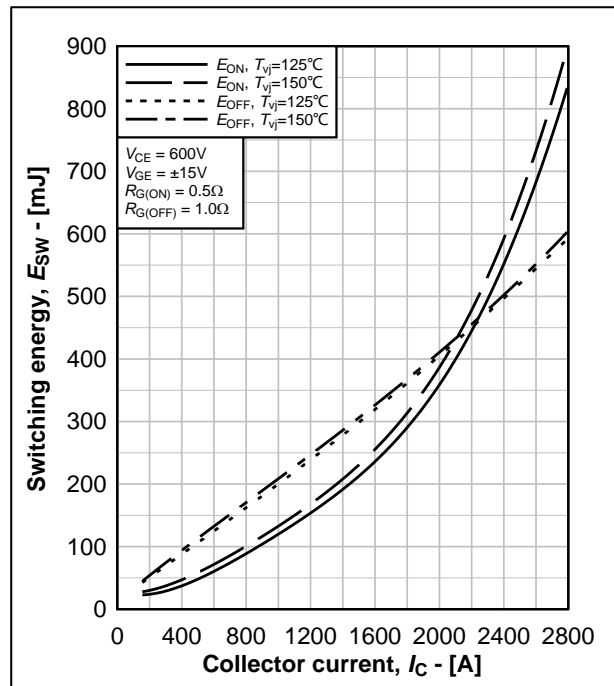


图 10. IGBT 开关能耗典型曲线, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$ Fig.10
Typical IGBT switching energy, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$

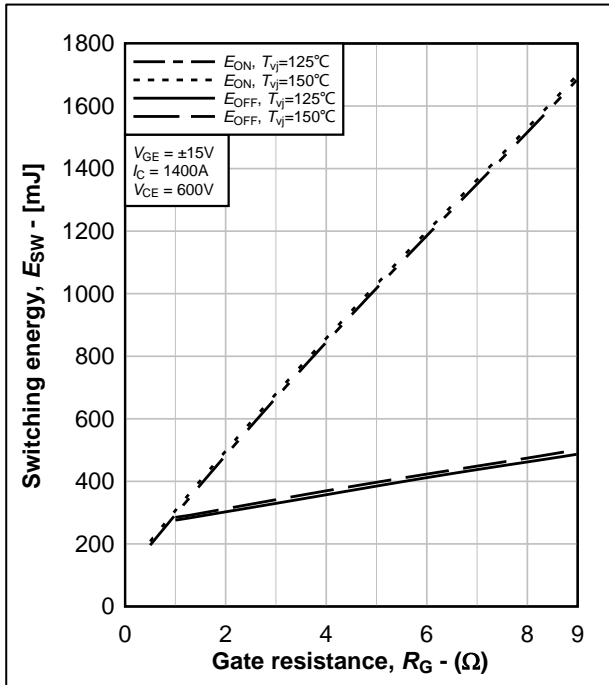


图 11. IGBT 开关能耗典型曲线, $E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 Fig.11 Typical IGBT switching energy,
 $E_{on} = f(R_G)$, $E_{off} = f(R_G)$

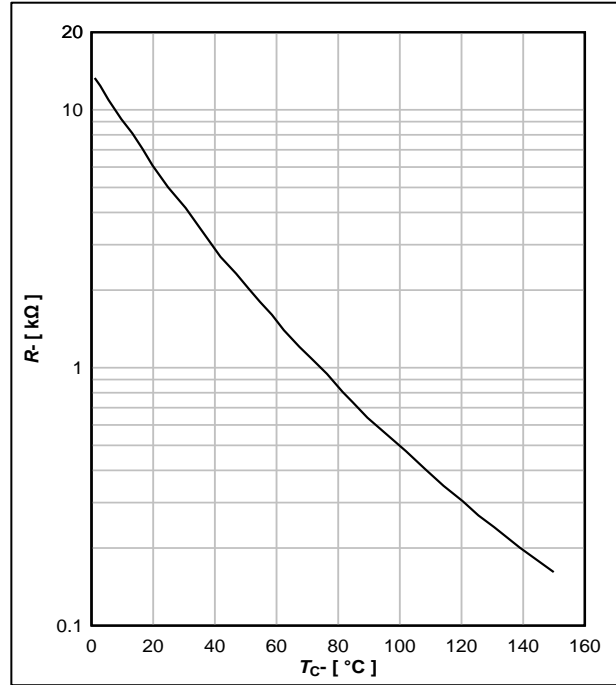


图 12. 热敏电阻典型特性曲线, $R = f(T_C)$
 Fig.12 Typical NTC thermistor characteristic, $R = f(T_C)$

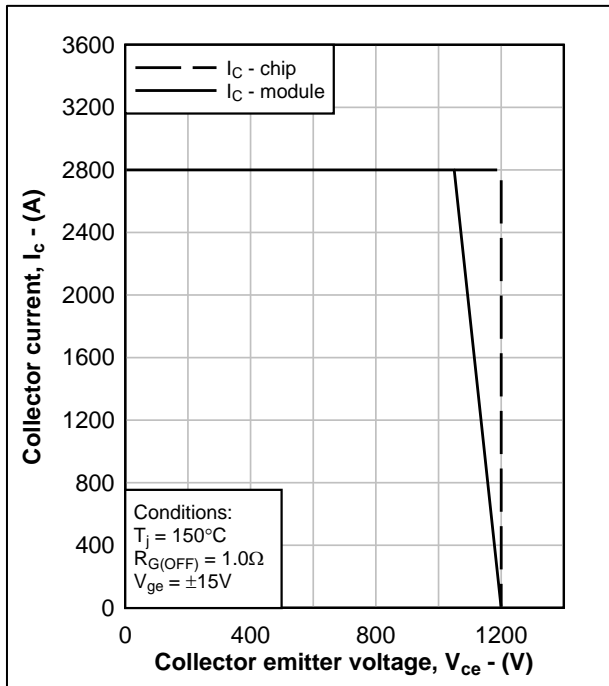


图 13. IGBT 反偏安全工作区, $I_c = f(V_{CE})$
 Fig.13 Reverse bias safe operating area of IGBT,
 $I_c = f(V_{CE})$

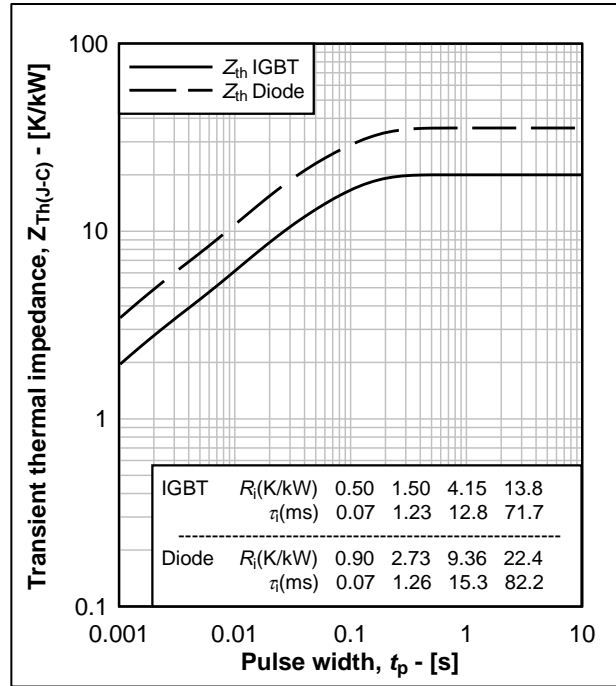
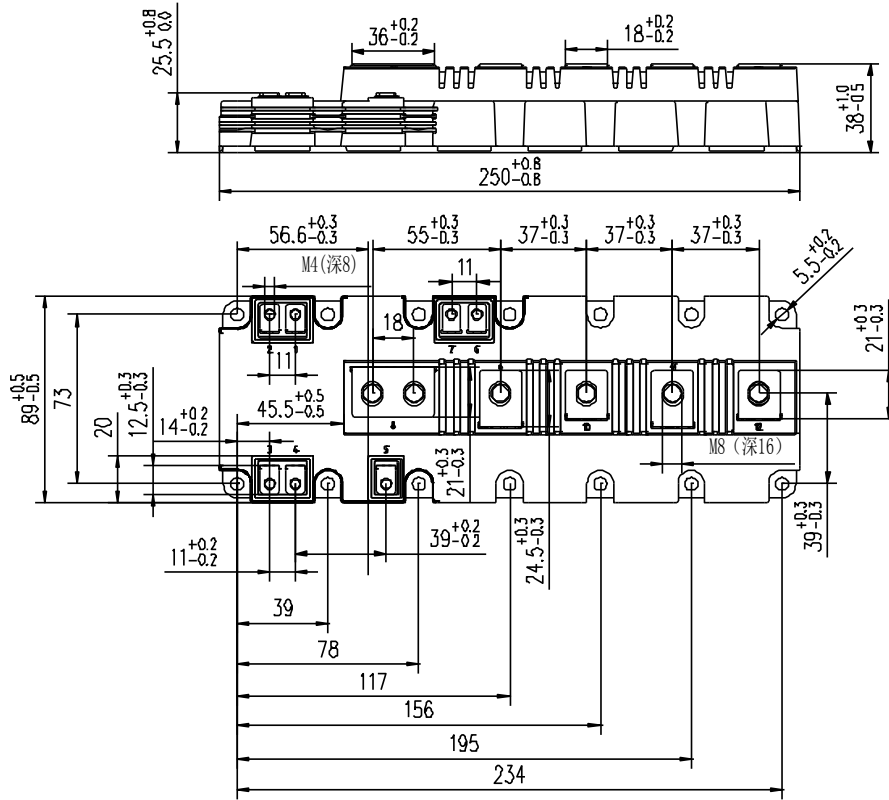


图 14. 瞬态热阻抗曲线, $Z_{Th(J-C)} = f(t)$
 Fig.14 Transient thermal impedance, $Z_{Th(J-C)} = f(t)$



重量 Weight: 1200g 模块外观类型 Module outline code: H1

图 14. 模块外观尺寸

Fig. 14 Module outlines

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